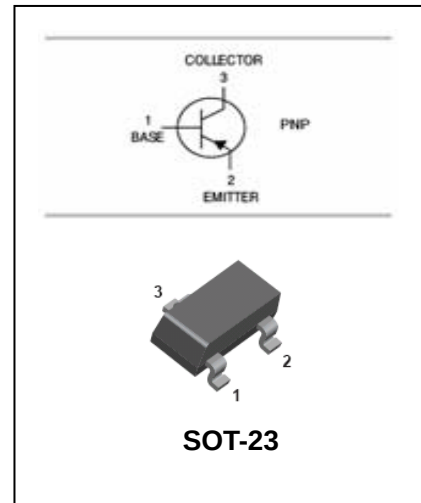


PNP General Purpose Transistor

MMBTA63/MMBTA64

FEATURES

- Epitaxial planar die construction.
- Complementary NPN type available (MMBTA13/MMBTA14).
- High current gain.



APPLICATIONS

- Ideal for medium power amplification and switching

ORDERING INFORMATION

Type No.	Marking	Package Code
MMBTA63	2U	SOT-23
MMBTA64	2V	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	UNIT	
V _{CBO}	collector-base voltage	MMBTA63	-30	V
		MMBTA64	-30	
V _{CEO}	collector-emitter voltage	MMBTA63	-30	V
		MMBTA64	-30	
V _{EBO}	emitter-base voltage		-10	V
I _C	collector current (DC)		-0.3	A
P _C	Collector dissipation		0.35	W
R _{θJA}	Thermal Resistance, Junction to Ambient		357	°C/W
T _j , T _{stg}	junction and storage temperature		-55-150	°C

PNP General Purpose Transistor

MMBTA63/MMBTA64

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Symbol	Parameter	Test conditions	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage MMBTA63 MMBTA64	$I_C = -100\mu A, I_E = 0$	-30 -30	-	V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage MMBTA63 MMBTA64	$I_C = -0.1mA, I_B = 0$	-30 -30	-	V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -100\mu A, I_C = 0$	-10	-	V
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30V$	-	-0.1	μA
I_{CEO}	collector cut-off current	$I_E = 0; V_{CE} = -10V$	-	-0.1	μA
h_{FE}	DC current gain MMBTA63 MMBTA64 MMBTA63 MMBTA64	$V_{CE} = -5V; I_C = -10mA$ $V_{CE} = -5V; I_C = -10mA$ $V_{CE} = -5V; I_C = -100mA$ $V_{CE} = -5V; I_C = -100mA$	5000 10000 10000 20000	-	
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C = -100mA; I_B = -0.1mA$	-	-1.5	V
f_T	transition frequency	$I_C = -10mA; V_{CE} = -5.0V;$ $f = 100MHz$	125	-	MHz

PACKAGE OUTLINE

Plastic surface mounted package

SOT-23

Top view of the SOT-23 package. Dimension A is the total width. Dimension B is the width of the main body. Dimension C is the width of the base. Dimension D is the width of the base. Dimension E is the width of the base. Dimension G is the width of the base. Dimension H is the height of the base. Dimension J is the height of the base. Dimension K is the total height.

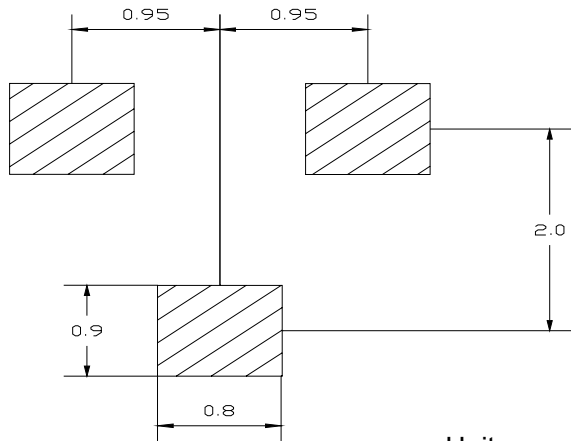
Side view of the SOT-23 package. Dimension A is the total width. Dimension B is the width of the main body. Dimension C is the width of the base. Dimension D is the width of the base. Dimension E is the width of the base. Dimension G is the width of the base. Dimension H is the height of the base. Dimension J is the height of the base. Dimension K is the total height.

Bottom view of the SOT-23 package. Dimension A is the total width. Dimension B is the width of the main body. Dimension C is the width of the base. Dimension D is the width of the base. Dimension E is the width of the base. Dimension G is the width of the base. Dimension H is the height of the base. Dimension J is the height of the base. Dimension K is the total height.

SOT-23		
Dim	Min	Max
A	2.85	2.95
B	1.25	1.35
C	1.0Typical	
D	0.37	0.43
E	0.35	0.48
G	1.85	1.95
H	0.02	0.1
J	0.1Typical	
K	2.35	2.45
All Dimensions in mm		

PNP General Purpose Transistor

MMBTA63/MMBTA64

SOLDERING FOOTPRINT

Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
MMBTA63/MMBTA64	SOT-23	3000/Tape&Reel